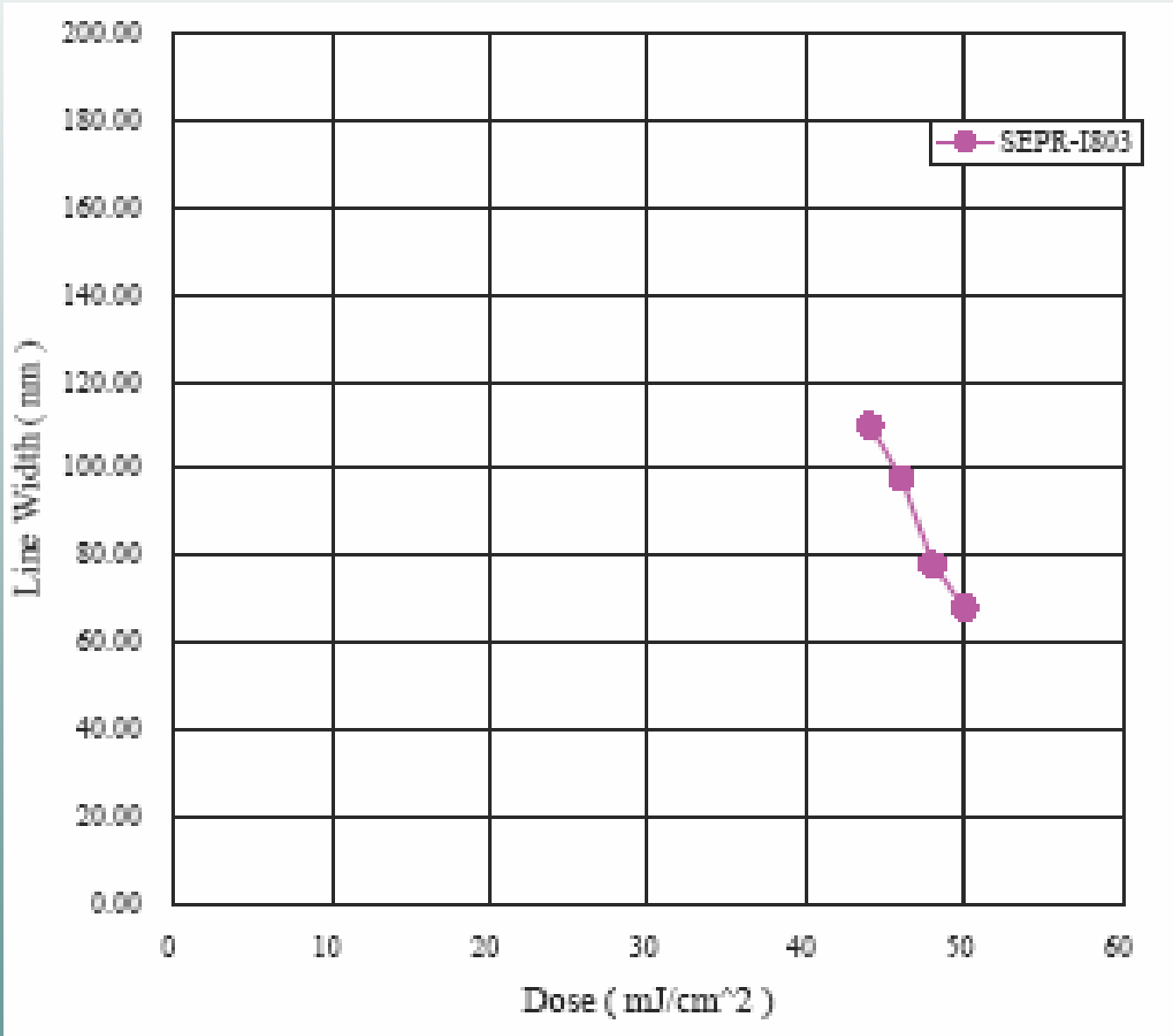
ShinEtsuMicroSi

SEPR – I803

SEPR-I803 Exposure Latitude (Mask : 100nm)

DUV-44 on Si Substrate

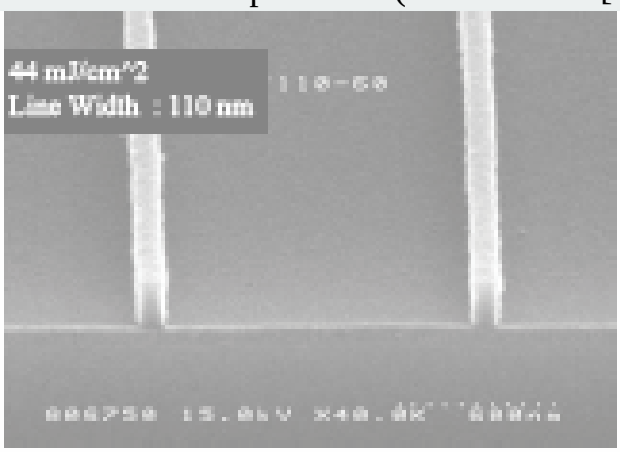
Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: (NSR-S203B , NA = 0.68, σ = 0.75)
Mask: 100nm Line Focus: -1.0 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddles (SSFD-238N [TMAH = 2.38%])

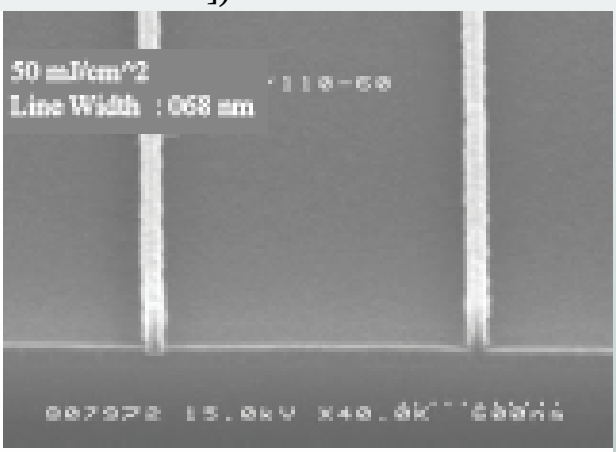


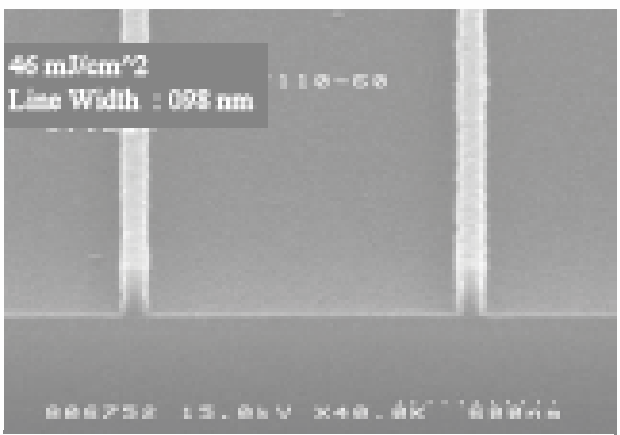
SEPR-I803
Exposure Latitude
DUV-44 on Si Substrate

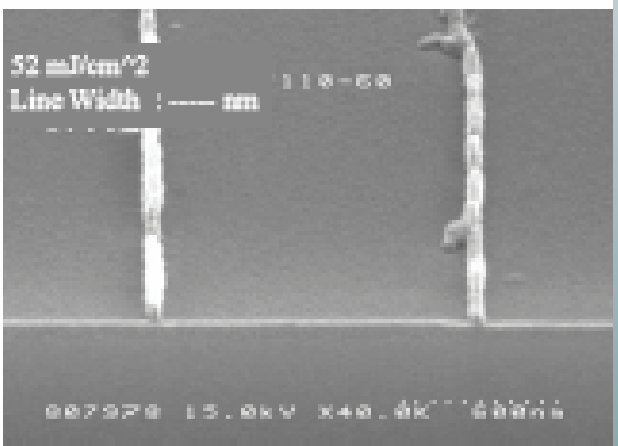
(FT:250 nm , Mask : 100nm)

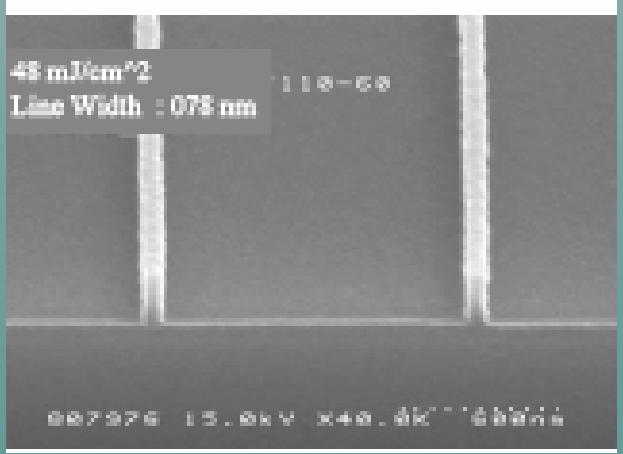
Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 44, 46, 48, 50, 52mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask: 100nm Line Focus: -1.0 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddles (SSFD-238N [TMAH = 2.38%])







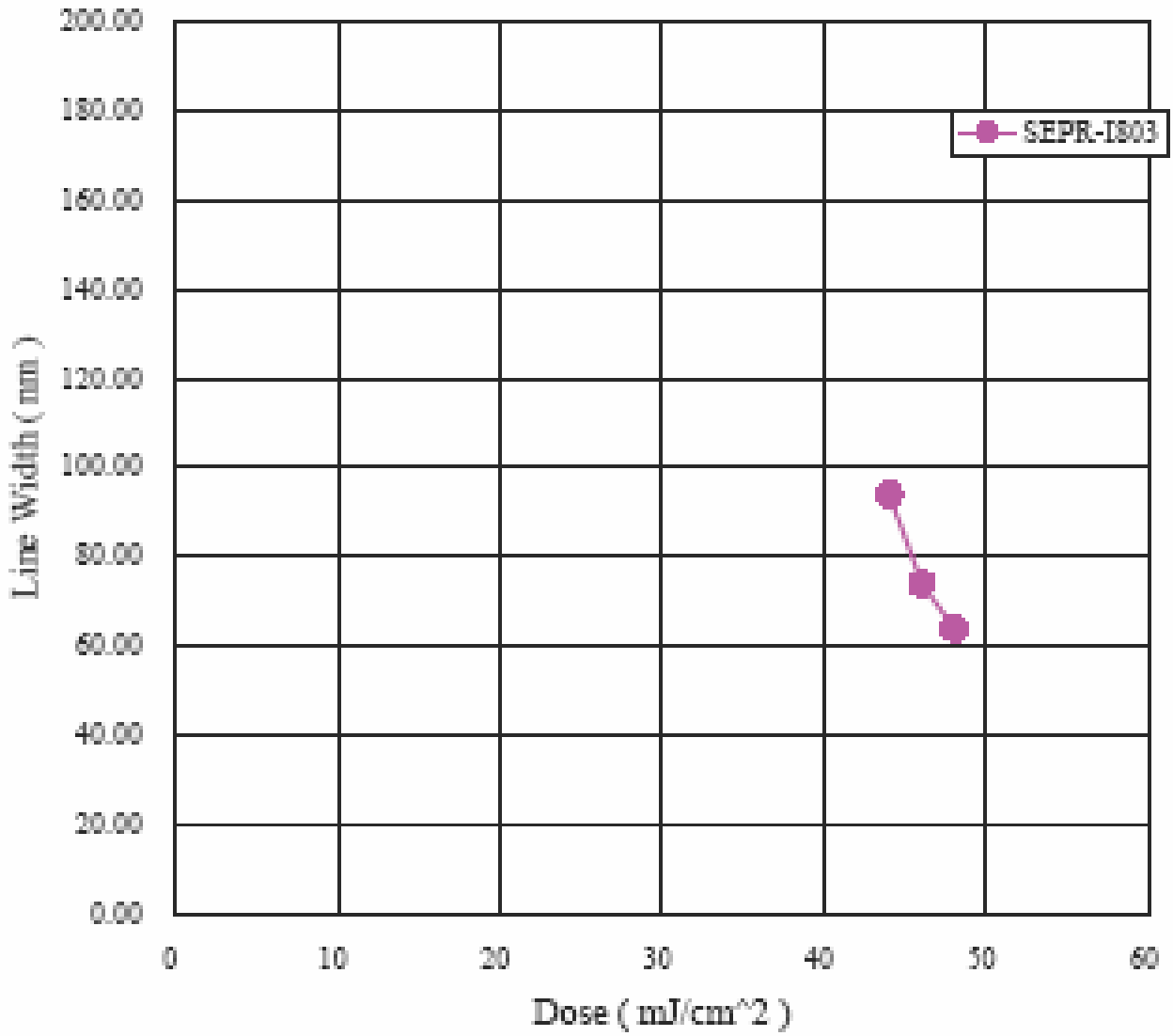




SEPR-I803 Exposure Latitude (Mask : 090nm)

DUV-44 on Si Substrate

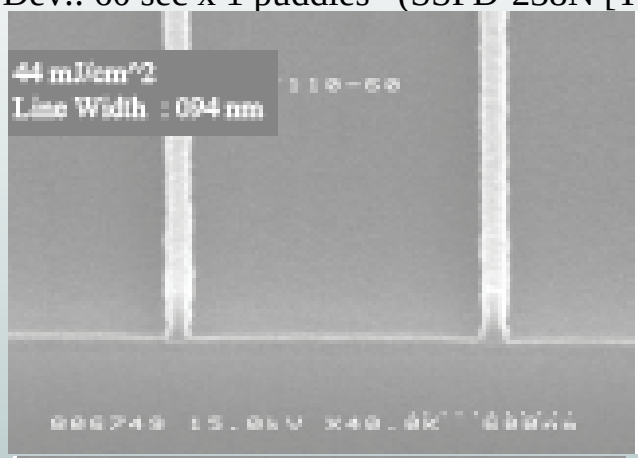
Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: (NSR-S203B NA = 0.68, σ = 0.75)
Mask: 90nm Line Focus: -1.0 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddles (SSFD-238N [TMAH = 2.38%])

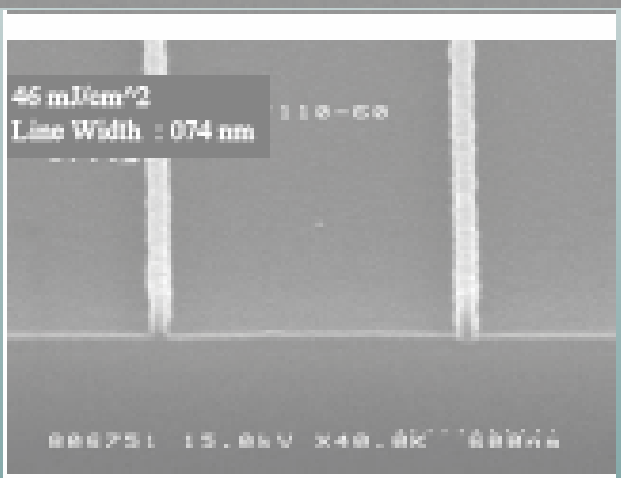


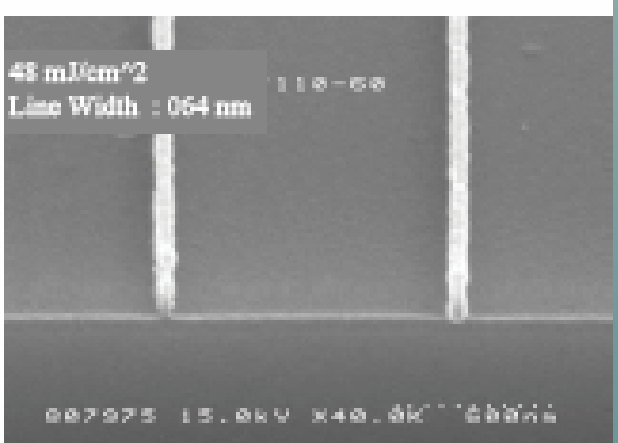
SEPR-I803
Exposure Latitude
DUV-44 on Si Substrate

(FT:250 nm , Mask : 90nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 44, 46, 48, 50, mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask: 90nm Line Focus: -1.0 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddles (SSFD-238N [TMAH = 2.38%])

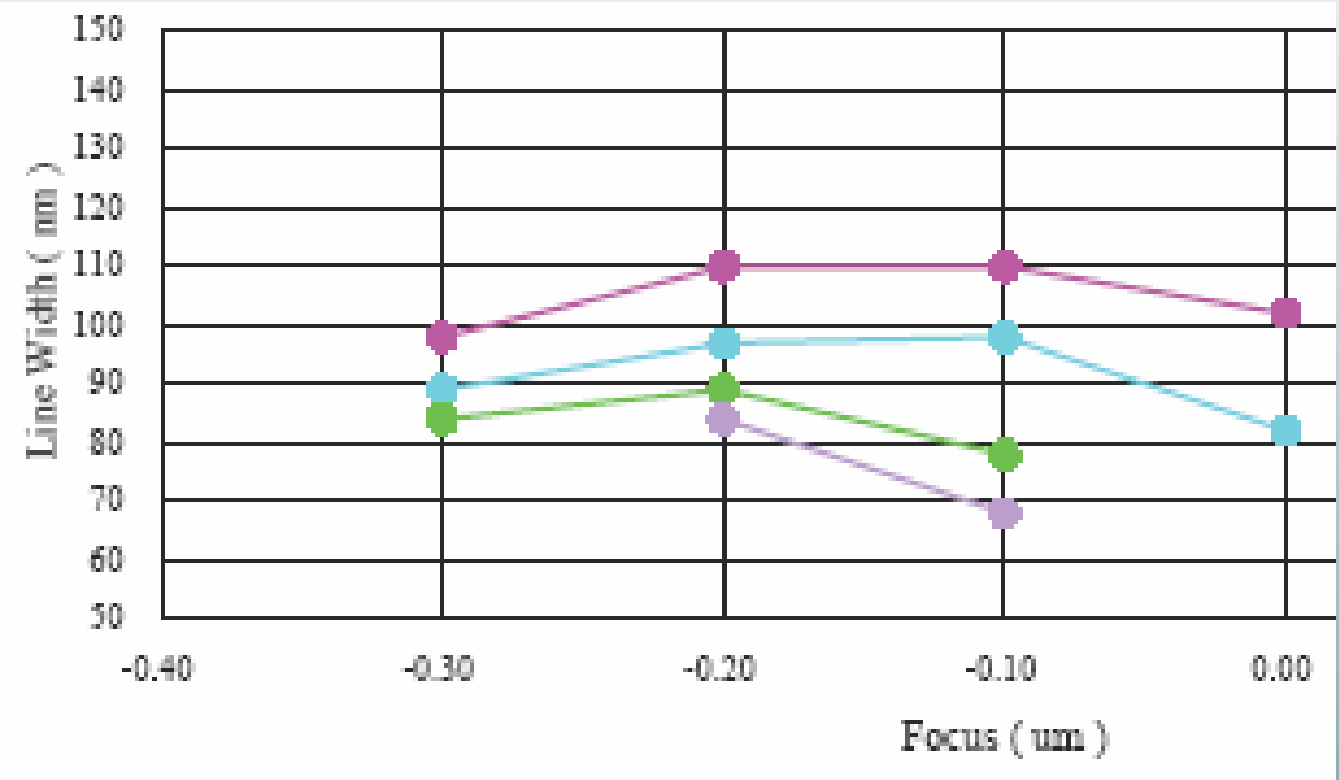






SEPR- I803 DOF (Mask : 100nm) DUV-44 on Si Substrate

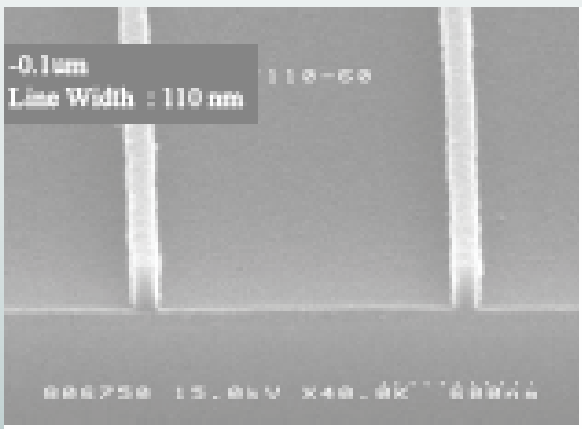
Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:100nm Line Focus: -0.4~+0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])

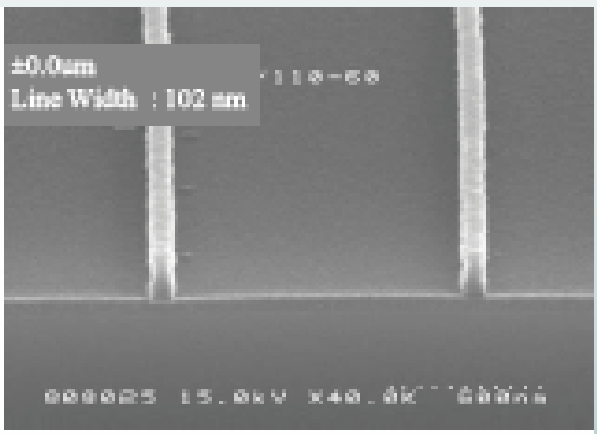


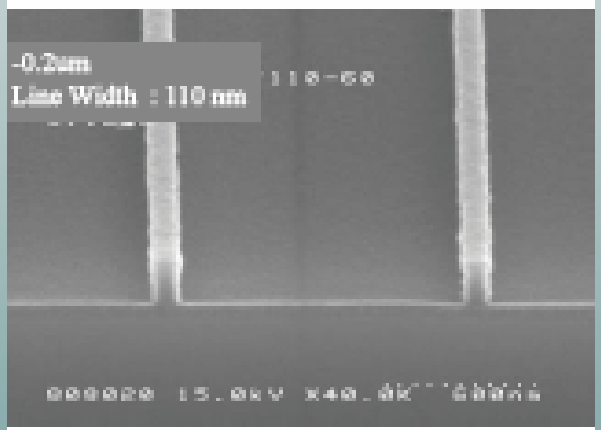
SEPR- I803 DOF DUV-44 on Si Substrate

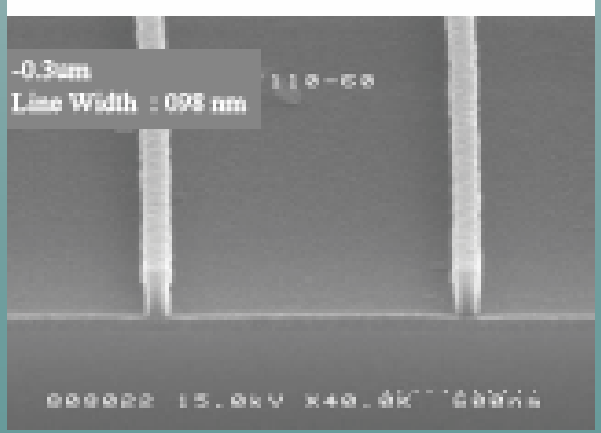
(FT:250 , Mask : 100nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 44mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:100nm Line Focus: -0.3 ~ +0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])





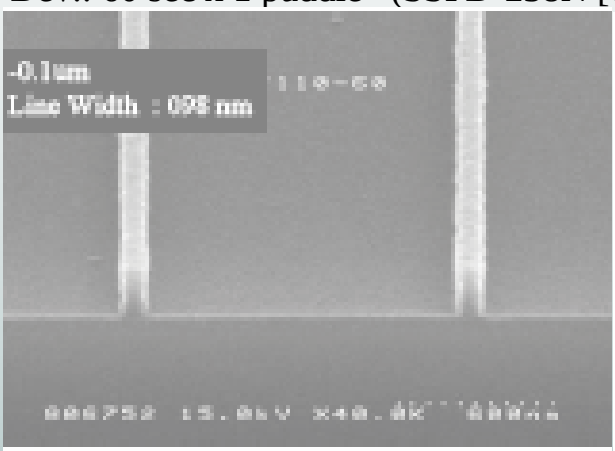


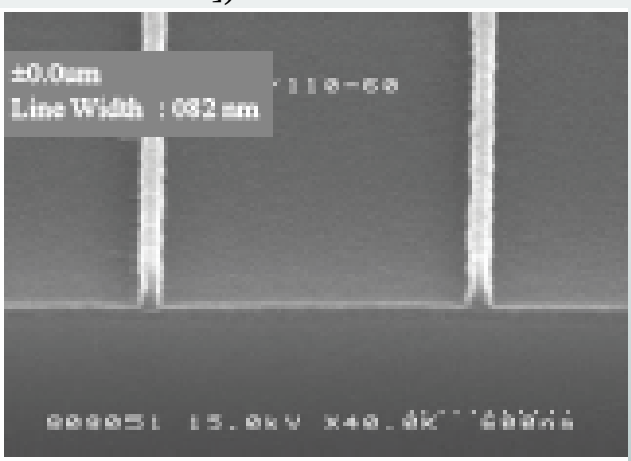


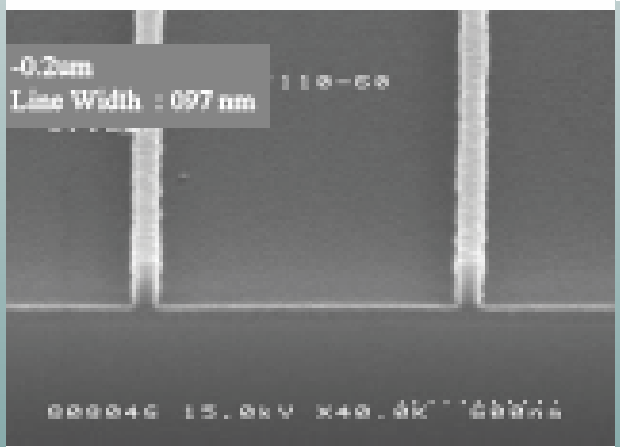
SEPR- I803 DOF DUV-44 on Si Substrate

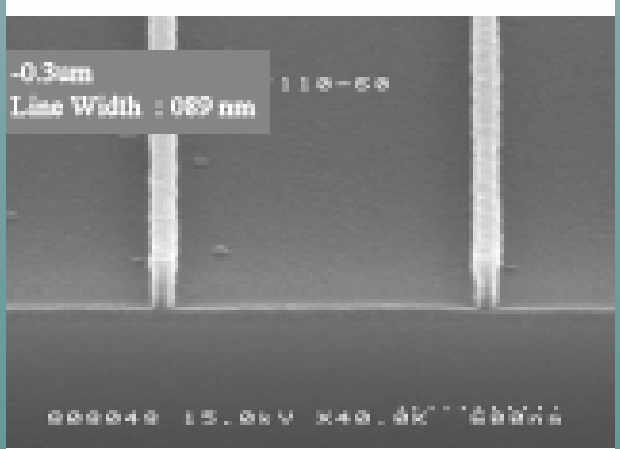
(FT:250 , Mask : 100nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 46mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:100nm Line Focus: -0.3 ~ +0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])





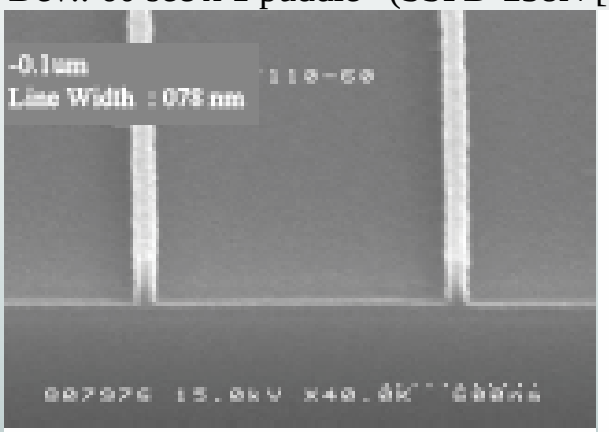


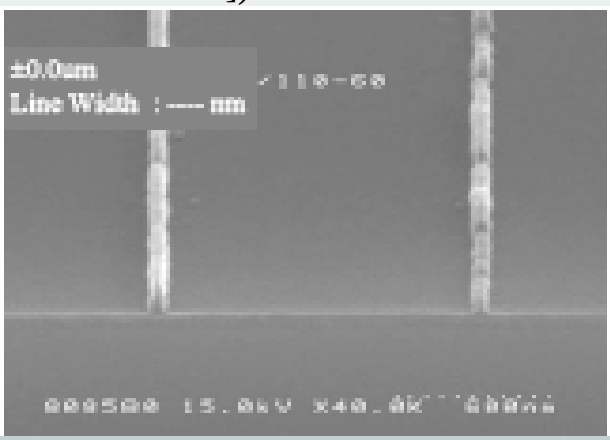


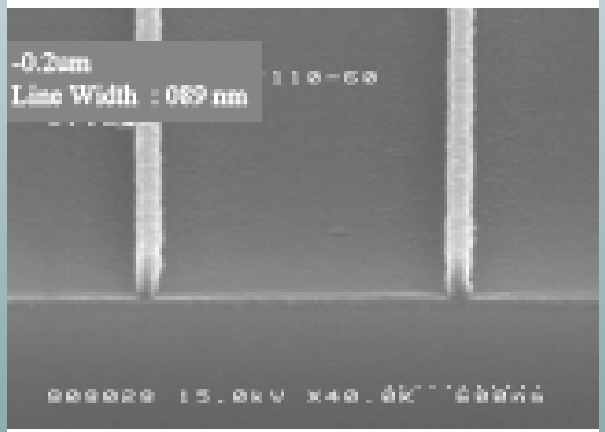
SEPR- I803 DOF DUV-44 on Si Substrate

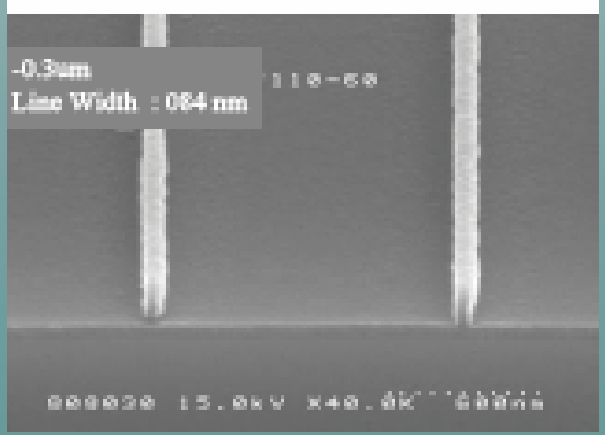
(FT:250 , Mask : 100nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 48mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:100nm Line Focus: -0.3 ~ +0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])





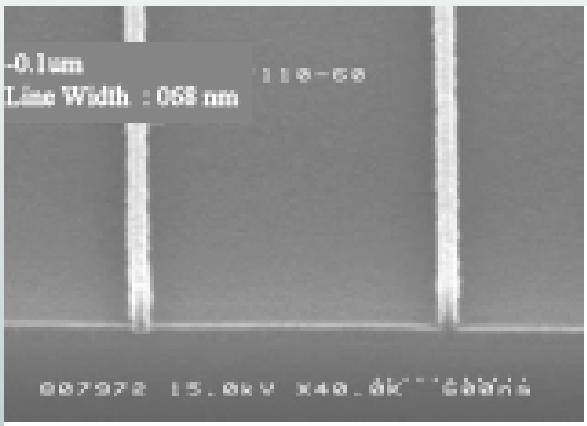


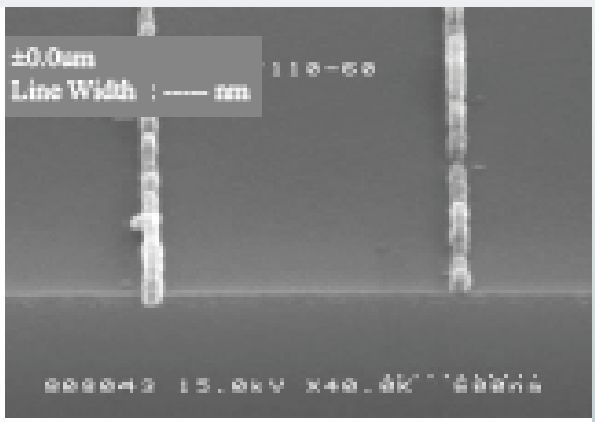


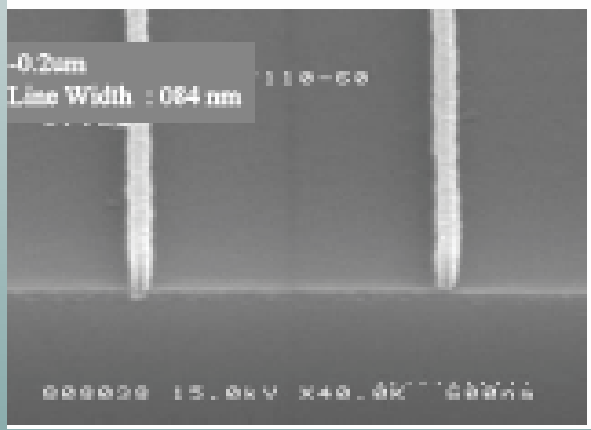
SEPR- I803 DOF DUV-44 on Si Substrate

(FT:250 , Mask : 100nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 50mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:100nm Line Focus: -0.3 ~ +0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])

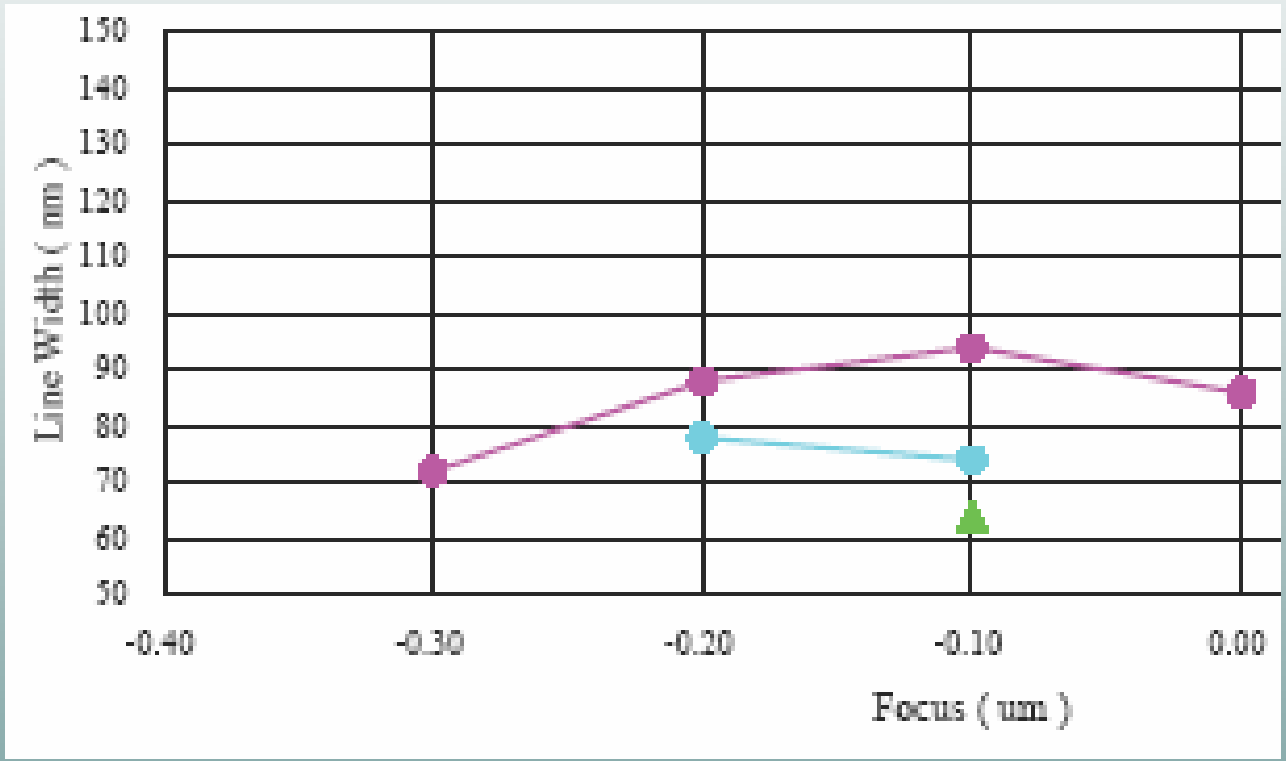






SEPR- I803 DOF (Mask : 90nm) DUV-44 on Si Substrate

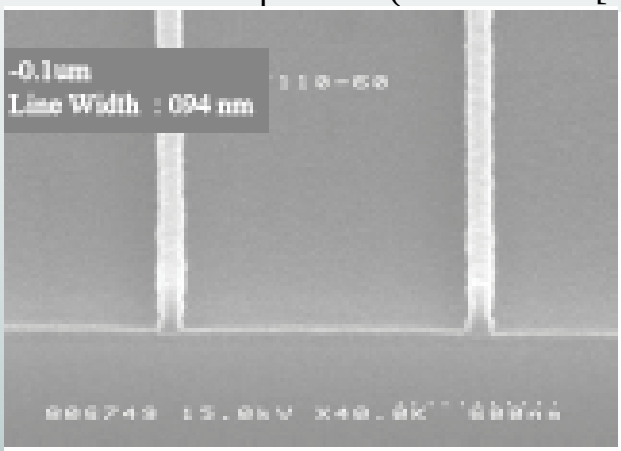
Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:90nm Line Focus: -0.4~+0.2 μm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])

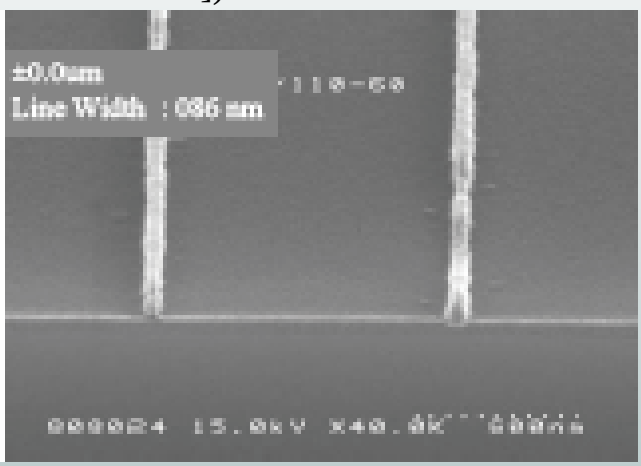


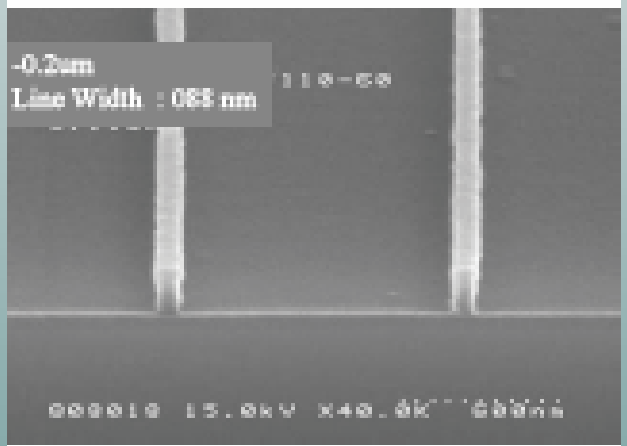
SEPR- I803 DOF DUV-44 on Si Substrate

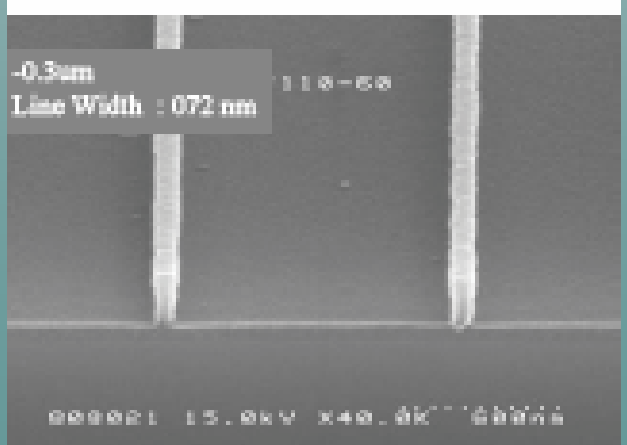
(FT:250 , Mask : 90nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 44mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:90nm Line Focus: -0.3 ~ +0.2 μm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])





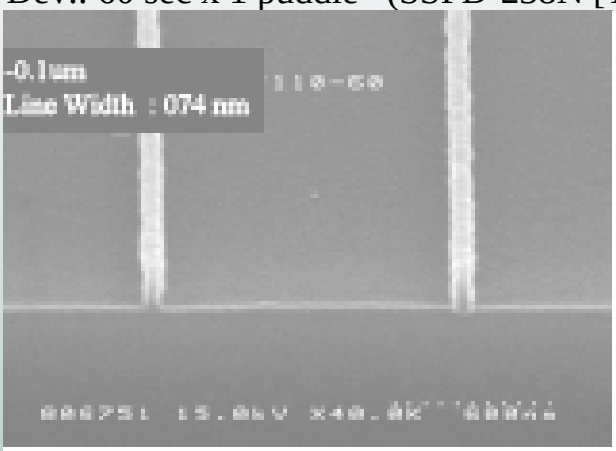


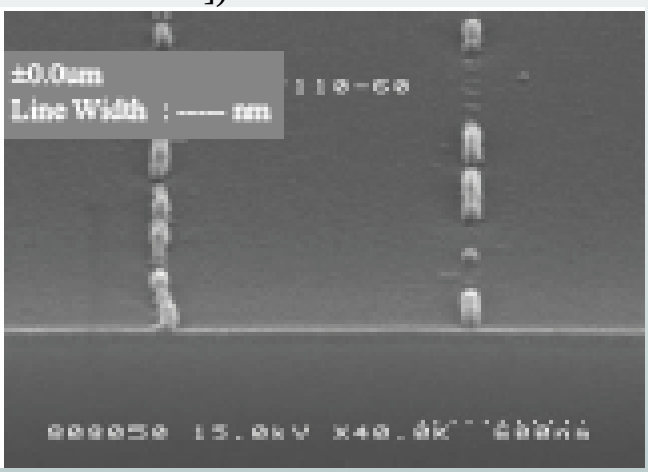


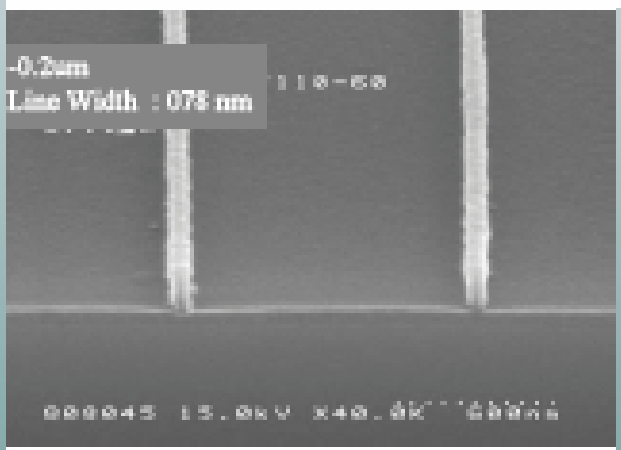
SEPR- I803 DOF DUV-44 on Si Substrate

(FT:250 , Mask : 90nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 46mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:90nm Line Focus: -0.3 ~ +0.2 μm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])







SEPR- I803 DOF DUV-44 on Si Substrate

(FT:250 , Mask : 90nm)

Film Thickness:250nm Prebake: 110°Cx90 sec
Exp.: 48mJ/cm^2 (NSR-S203B , NA = 0.68, σ = 0.75)
Mask:90nm Line Focus: -0.3 ~ +0.2 µm PEB: 110°C x 90 sec
Dev.: 60 sec x 1 puddle (SSFD-238N [TMAH = 2.38%])